L Number	Hits	Search Text	DB	Time stamp
1	89	((((BARC or ARC or antireflect\$4 or anti	USPAT;	2003/08/30 10:52
		adj reflect\$4) same (resist or	US-PGPUB;	
		photoresist) same (IMD or dielectric)) and	EPO; JPO;	
		(BARC or ARC or antireflect\$4 or anti adj	IBM TDB	
		reflect\$4) near3 (conformal or via or	_	
		opening or trench or groove or sidewall))		
		and (BARC or ARC or antireflect\$4 or anti		
		adj reflect\$4) same etch\$3 near2 stop\$4)		
		and (BARC or ARC or antireflect\$4 or anti		
		adj reflect\$4) same (silicon adj		
		oxynitride or "SiON" or titanium adj		
		nitride or "Ti.sub."?"N.sub."? or "TiN" or		
		"Ti" adj "N")		
2	20	1	USPAT;	2003/08/30 11:13
_		adj reflect\$4) same (resist or	US-PGPUB;	
		photoresist) same (IMD or dielectric)) and	EPO; JPO;	
		(BARC or ARC or antireflect\$4 or anti adj	IBM TDB	
		reflect\$4) near3 (conformal or via or	_	
		opening or trench or groove or sidewall))		
		and (BARC or ARC or antireflect\$4 or anti	1	
	!	adj reflect\$4) same etch\$3 near2 stop\$4)		
		not (((((BARC or ARC or antireflect\$4 or		,
		anti adi reflect\$4) same (resist or		
		photoresist) same (IMD or dielectric)) and		,
}		(BARC or ARC or antireflect\$4 or anti adj		
		reflect\$4) near3 (conformal or via or		
		opening or trench or groove or sidewall))		
		and (BARC or ARC or antireflect\$4 or anti		
		adj reflect\$4) same etch\$3 near2 stop\$4)		
		and (BARC or ARC or antireflect\$4 or anti		
		adj reflect\$4) same (silicon adj		
		oxynitride or "SiON" or titanium adj		
		nitride or "Ti.sub."?"N.sub."? or "TiN" or		
		"Ti" adj "N"))		
3	86	(((BARC or ARC or antireflect\$4 or anti	USPAT;	2003/08/30 11:16
		adj reflect\$4) same (resist or	US-PGPUB;	
		photoresist) same (IMD or dielectric)) and	EPO; JPO;	,
		(BARC or ARC or antireflect\$4 or anti adj	IBM TDB	
		reflect\$4) near3 (conformal or via or	-	
		opening or trench or groove or sidewall))		
1		not ((((BARC or ARC or antireflect\$4 or	1	
		anti adj reflect\$4) same (resist or		
		photoresist) same (IMD or dielectric)) and		
		(BARC or ARC or antireflect\$4 or anti adj	1	
	1	reflect\$4) near3 (conformal or via or		
		opening or trench or groove or sidewall))	1	
		and (BARC or ARC or antireflect\$4 or anti	1	
		adj reflect\$4) same etch\$3 near2 stop\$4)		
4	816	((BARC or ARC or antireflect\$4 or anti adj	USPAT;	2003/08/30 11:24
		reflect\$4) same (resist or photoresist)	US-PGPUB;	
		same (IMD or dielectric)) not (((BARC or	EPO; JPO;	
		ARC or antireflect\$4 or anti adj	IBM_TDB	
		reflect\$4) same (resist or photoresist)	_	
		same (IMD or dielectric)) and (BARC or ARC		
		or antireflect\$4 or anti adj reflect\$4)		
		near3 (conformal or via or opening or		
		trench or groove or sidewall))		
5	9	((BARC or ARC or antireflect\$4 or anti adj	USPAT;	2003/08/30 17:01
		reflect\$4) with (via or hole or wall or	US-PGPUB;	
!		sidewall or opening or trench)) and	EPO; JPO;	
	1	427/97.ccls.	IBM TDB	l .

6	0	430/311,313,317,950.ccls. and (DARC or TARC or BARC or ARC or antireflect\$4 or anti adj reflect\$4) near5 (sidewall or side adj wall or hole adj wall or via near2 wall or via near2 side or trench near2 wall or trench near2 side or conformal\$3) same (IMD or ILD or dielectric) not ((BARC or ARC or antireflect\$4) same	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/30 17:03
		(resist or photoresist) same (IMD or		
7	0	dielectric)) 430/311,313,317,950.ccls. and (DARC or TARC or BARC or ARC or antireflect\$4 or anti adj reflect\$4) near5 (sidewall or side adj wall or hole adj wall or via	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/08/30 17:04
		near2 wall or via near2 side or trench near2 wall or trench near2 side or conformal\$3) and (IMD or ILD or dielectric) not ((BARC or ARC or antireflect\$4 or anti adj reflect\$4) same (resist or photoresist) same (IMD or	-	
8	0	dielectric)) (430/311,313,317,950.ccls. and (DARC or	USPAT;	2003/08/30 17:06
		TARC or BARC or ARC or antireflect\$4 or anti adj reflect\$4) near5 (sidewall or	US-PGPUB; EPO; JPO;	
		side adj wall or hole adj wall or via near2 wall or via near2 side or trench	IBM_TDB	
		near2 wall or trench near2 side or conformal\$3) and (IMD or ILD or		
	`	dielectric)) not ((BARC or ARC or antireflect\$4) same		
		(resist or photoresist) same (IMD or dielectric))		
-	2	(("6297168") or ("6383943")).PN.	USPAT; US-PGPUB	2003/01/27 14:02
_	883	(BARC or ARC or antireflect\$4 or anti adj reflect\$4) same (resist or photoresist) same (IMD or dielectric)	USPAT; US-PGPUB; EPO; JPO;	2003/04/21 18:45
-	169	((BARC or ARC or antireflect\$4 or anti adj reflect\$4) same (resist or photoresist) same (IMD or dielectric)) and (BARC or ARC or antireflect\$4 or anti adj reflect\$4) near3 (conformal or via or opening or trench or groove or sidewall)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/18 17:10
-	94	(((BARC or ARC or antireflect\$4 or anti adj reflect\$4) same (resist or	USPAT; US-PGPUB;	2003/04/18 17:12
		photoresist) same (IMD or dielectric)) and (BARC or ARC or antireflect\$4 or anti adj reflect\$4) near3 (conformal or via or	EPO; JPO; IBM_TDB	
		opening or trench or groove or sidewall)) and (BARC or ARC or antireflect\$4 or anti adj reflect\$4) same etch\$3 near2 stop\$4		
_	75		USPAT; US-PGPUB; EPO; JPO;	2003/08/30 10:51
		(BARC or ARC or antireflect\$4 or anti adj reflect\$4) near3 (conformal or via or	IBM_TDB	
		opening or trench or groove or sidewall)) and (BARC or ARC or antireflect\$4 or anti adj reflect\$4) same etch\$3 near2 stop\$4)		
		and (BARC or ARC or antireflect\$4 or anti adj reflect\$4) same (silicon adj		
		oxynitride or "SiON" or titanium adj nitride or "Ti.sub."?"N.sub."? or "TiN" or		
		"Ti" adj "N")		

		_		
<u> </u>	19	((((BARC or ARC or antireflect\$4 or anti	USPAT;	2003/08/30 11:12
		adj reflect\$4) same (resist or	US-PGPUB;	
İ		photoresist) same (IMD or dielectric)) and	EPO; JPO;	
		(BARC or ARC or antireflect\$4 or anti adj	IBM_TDB	
	1	reflect\$4) near3 (conformal or via or		
		opening or trench or groove or sidewall))		
		and (BARC or ARC or antireflect\$4 or anti		
		adj reflect\$4) same etch\$3 near2 stop\$4)		
		not ((((BARC or ARC or antireflect\$4 or		
		anti adj reflect\$4) same (resist or		İ
		photoresist) same (IMD or dielectric)) and		
		(BARC or ARC or antireflect\$4 or anti adj		
		reflect\$4) near3 (conformal or via or		
		opening or trench or groove or sidewall)) and (BARC or ARC or antireflect\$4 or anti		
		adj reflect\$4) same etch\$3 near2 stop\$4) and (BARC or ARC or antireflect\$4 or anti		
		and (BARC of ARC of antiferrects4 of anti-		
		oxynitride or "SiON" or titanium adj nitride or "Ti.sub."?"N.sub."? or "TiN" or		
		Ti" adj "N"))		
_	75	1	USPAT;	2003/08/30 11:15
-	'3	(((BARC OF ARC OF ARCITETIECT) 4 OF ARCI	US-PGPUB;	2003/00/30 11:13
		photoresist) same (IMD or dielectric)) and	EPO; JPO;	
		(BARC or ARC or antireflect\$4 or anti adj	IBM TDB	
		reflect\$4) near3 (conformal or via or	100-100	
•		opening or trench or groove or sidewall))		
		not (((BARC or ARC or antireflect\$4 or		
]	anti adj reflect\$4) same (resist or	ĺ	
	1	photoresist) same (IMD or dielectric)) and		
		(BARC or ARC or antireflect\$4 or anti adj		
		reflect\$4) near3 (conformal or via or		
	1	opening or trench or groove or sidewall))		
		and (BARC or ARC or antireflect\$4 or anti		
		adj reflect\$4) same etch\$3 near2 stop\$4)		•
_	714	((BARC or ARC or antireflect\$4 or anti adj	USPAT;	2003/08/30 11:23
		reflect\$4) same (resist or photoresist)	US-PGPUB;	2000,00,00 22.20
		same (IMD or dielectric)) not (((BARC or	EPO; JPO;	
		ARC or antireflect\$4 or anti adj	IBM TDB	
		reflect\$4) same (resist or photoresist)	_	
		same (IMD or dielectric)) and (BARC or ARC		
		or antireflect\$4 or anti adj reflect\$4)		
		near3 (conformal or via or opening or		İ
		trench or groove or sidewall))		
-	42789	(BARC or ARC or antireflect\$4 or anti adj	USPAT;	2003/04/21 10:18
		reflect\$4) with (via or hole or wall or	US-PGPUB;	
1		sidewall or opening or trench)	EPO; JPO;	
			IBM_TDB	
-	9	, (USPAT;	2003/08/30 17:00
		reflect\$4) with (via or hole or wall or	US-PGPUB;	
		sidewall or opening or trench)) and	EPO; JPO;	
1		427/97.ccls.	IBM_TDB	
-	1	("6541367").PN.	USPAT;	2003/04/21 16:17
			US-PGPUB	
-	0	430/311,313,317,950.ccls. and (DARC or	USPAT;	2003/08/30 17:01
		TARC or BARC or ARC or antireflect\$4 or	US-PGPUB;	
1		anti adj reflect\$4) near5 (sidewall or	EPO; JPO;	
1]	side adj wall or hole adj wall or via	IBM_TDB	
1		near2 wall or via near2 side or trench		
1		near2 wall or trench near2 side or		
		conformal\$3) same (IMD or ILD or		
		dielectric) not ((BARC or ARC or		
		antireflect\$4 or anti adj reflect\$4) same		
		(resist or photoresist) same (IMD or		
L	L	dielectric))	L	l

	1 0	430/311,313,317,950.ccls. and (DARC or	USPAT;	2003/08/30 17:01
		TARC or BARC or ARC or antireflect\$4 or	US-PGPUB;	2000,00,00 1110
		anti adj reflect\$4) near5 (sidewall or	EPO; JPO;	
		side adj wall or hole adj wall or via	IBM TDB	
		near2 wall or via near2 side or trench	120,_100	
		near2 wall or trench near2 side or		
		conformal\$3) and (IMD or ILD or	1	
		dielectric) not ((BARC or ARC or		
		antireflect\$4 or anti adj reflect\$4) same		
		(resist or photoresist) same (IMD or		
		dielectric))		
_	0	(430/311,313,317,950.ccls. and (DARC or	USPAT;	2003/08/30 17:01
		TARC or BARC or ARC or antireflect\$4 or	US-PGPUB;	
		anti adj reflect\$4) near5 (sidewall or	EPO; JPO;	
		side adj wall or hole adj wall or via	IBM TDB	
		near2 wall or via near2 side or trench		
		near2 wall or trench near2 side or		
		conformal\$3) and (IMD or ILD or		
		dielectric)) not ((BARC or ARC or		
		antireflect\$4 or anti adj reflect\$4) same		
		(resist or photoresist) same (IMD or		
		dielectric))		

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